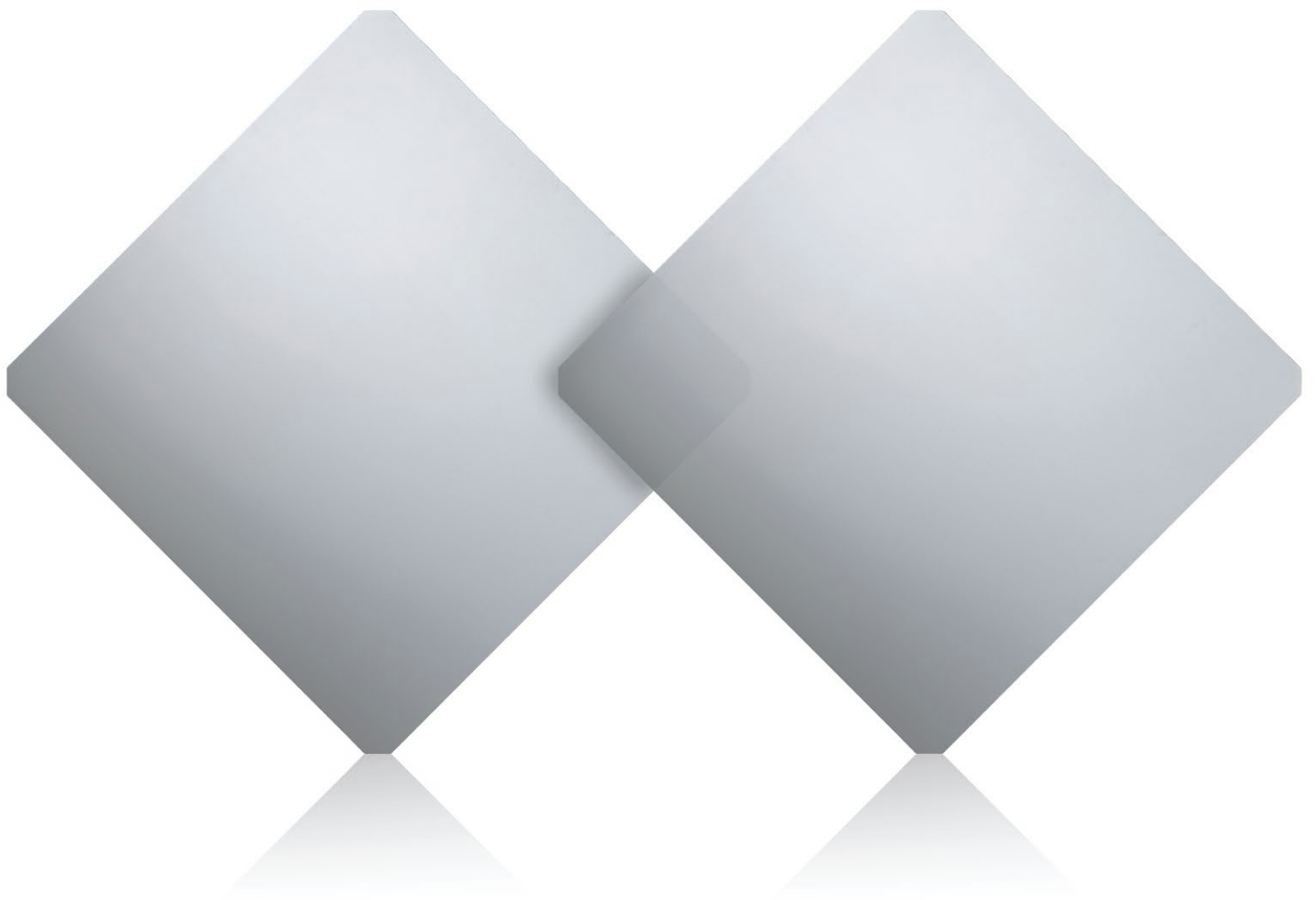


Monocrystalline Wafer

N-type-G12-R-Res 0.9~1.6-A Grade



Comprehensive system certification

ISO 9001:2015

ISO 14001:2015

OHSAS 18001:2018

Monocrystalline Wafer Specification

N-type-G12-R-Res0.9~1.6-A Grade

Key Parameters

Conductivity type	N-type	P/N type tester(DLY-2 P/N)
Dopant	Sb,P	--
Resistivity/ Ω .cm	0.9-1.6	Wafer inspection system
MCLT(Minority carrier lifetime)/ μ s	≥ 1000	QSSPC /Transient with injection level: $5E14 \text{ cm}^{-3}$ (Sinton BCT-400)
Oxygen concentration [O _i]/ at/cm ³	$\leq 6.0 \times 10^{17}$	FTIR (ASTM F121-83)
Carbon Concentration [C _s]/ at/cm ³	$\leq 5.0 \times 10^{16}$	FTIR (GB/T 1558-2009)

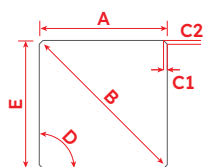
Material Properties

Growth method	CZ	--
Crystallinity	Monocrystalline	--
Etch pit density/ pcs/cm ²	≤ 500	Preferential Etch Techniques (ASTM F47-88)
Surface orientation/ $^{\circ}$	$\langle 100 \rangle \pm 2$	X-ray Diffraction Method (ASTM F26-1987)
Orientation of pseudo square sides/ $^{\circ}$	$\langle 010 \rangle, \langle 001 \rangle \pm 2$	X-ray Diffraction Method (ASTM F26-1987)

Geometric Dimensions and Surface Properties

Wafer model	G12-R	--
Geometry	Rectangular	--
Bevel edge shape	Straight	--
Wafer Side length/mm	Short 182.3 ± 0.20 ; Long 210 ± 0.20	Wafer inspection system
Wafer Diagonal line/mm	$\phi 272 \pm 0.20$	Wafer inspection system
Chamfer projection/mm	C1: 4.72 ± 0.57 ; C2: 4.07 ± 0.52	Wafer inspection system
Angle between adjacent sides/ $^{\circ}$	90 ± 0.15	Wafer inspection system
Thickness/ μ m	130 ± 8	Wafer inspection system
Batch mean/ μ m	≥ 130	Wafer inspection system
Total thickness variation/ μ m	≤ 20	Wafer inspection system
Saw marks / μ m	≤ 13	Wafer inspection system
Warp/ μ m	≤ 40	Wafer inspection system
Cutting method	DW	--
Surface quality	As cut and cleaned, no visible contamination, slight color difference is allowed; (oil or grease, finger prints, spot stains, epoxy/glue residue are not allowed)	Wafer inspection system
Chip	Depth ≤ 0.3 mm and length ≤ 0.5 mm, Max 1/pcs; no V-chip	Naked eyes or wafer inspection system
Micro cracks / holes	Not allowed	Wafer inspection system

Schematic diagram of wafer



Size: G12-R

A: 182.3 ± 0.20 mm	C1: 4.72 ± 0.57 mm
E: 210 ± 0.20 mm	C2: 4.07 ± 0.52 mm
B: $\phi 272 \pm 0.20$ mm	D: $90 \pm 0.15^{\circ}$

Specifications subjects to technical changes and test, Indosol Solar reserves the right of final interpretation.



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